

描述 / Descriptions

SOT-363 塑封封装双 NPN 半导体三极管。Double silicon NPN transistor in a SOT-363 Plastic Package.

特征 / Features

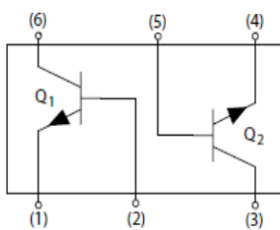
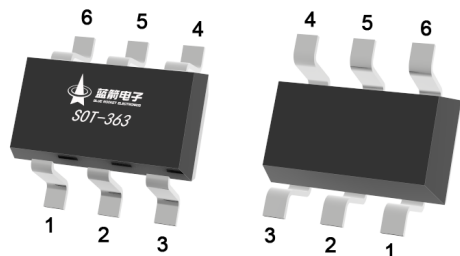
高电压,与 BRDBC856WSQ 互补,符合 AEC-Q101 标准高可靠性要求,无卤产品。

High voltage, complementary pair with BRDBC856WSQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

用途 / Applications

用于普通高压放大,满足汽车应用的严格要求。

General purpose high voltage amplifier, Meet the stringent requirements of automotive applications.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1、4 : Emitter

PIN 2、5 : Base

PIN 3、6 : Collector

放大及印章代码 / hFE Classifications & Marking

见印章说明。See Marking Instructions.

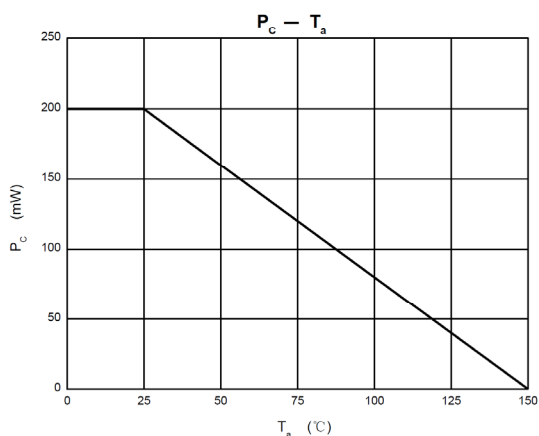
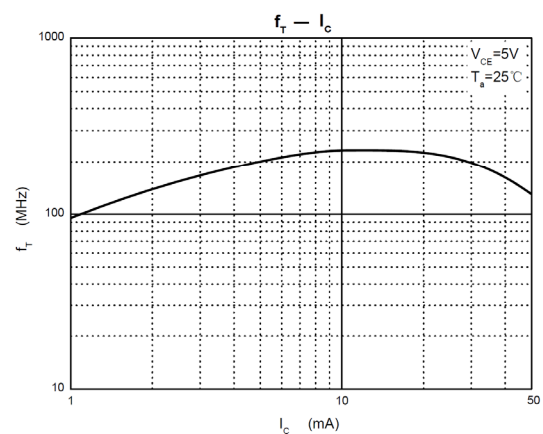
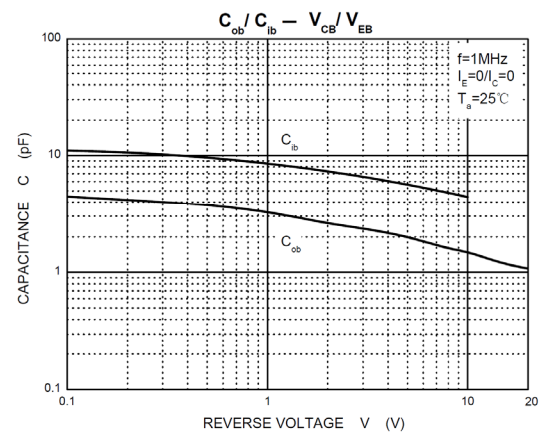
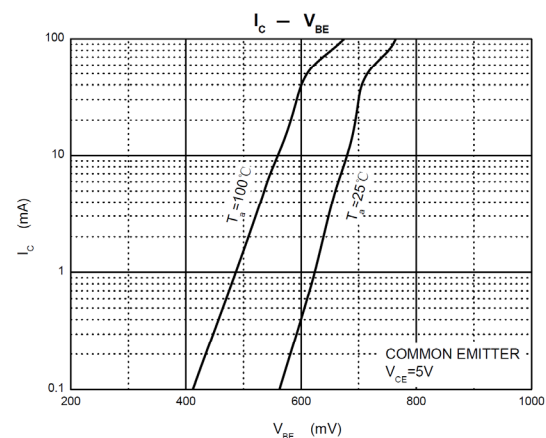
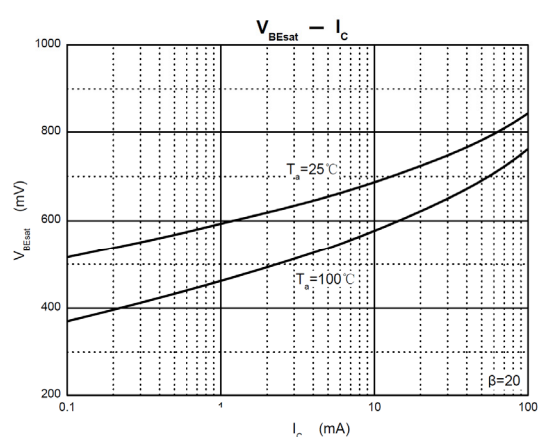
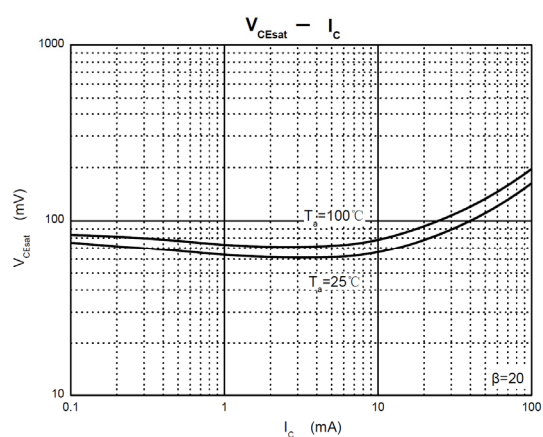
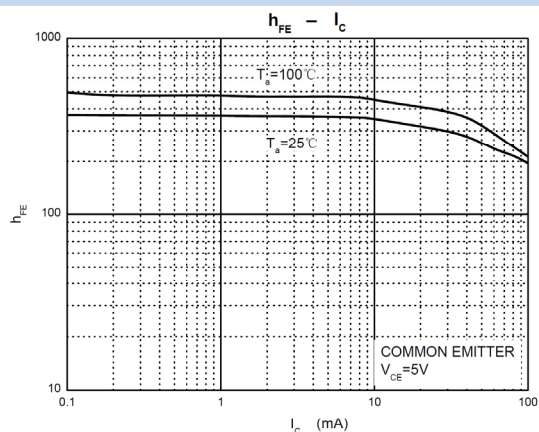
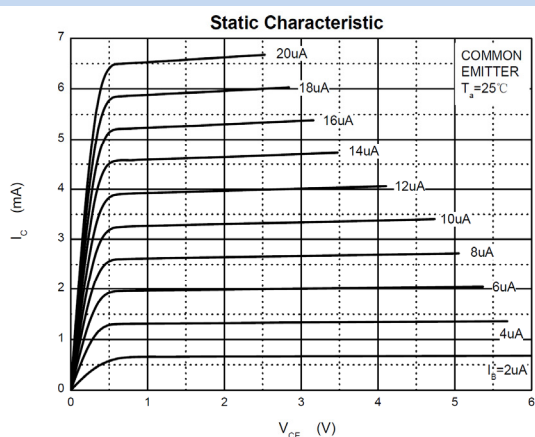
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V _{CBO}	80	V
Collector to Emitter Voltage	V _{CEO}	65	V
Emitter to Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	I _C	100	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

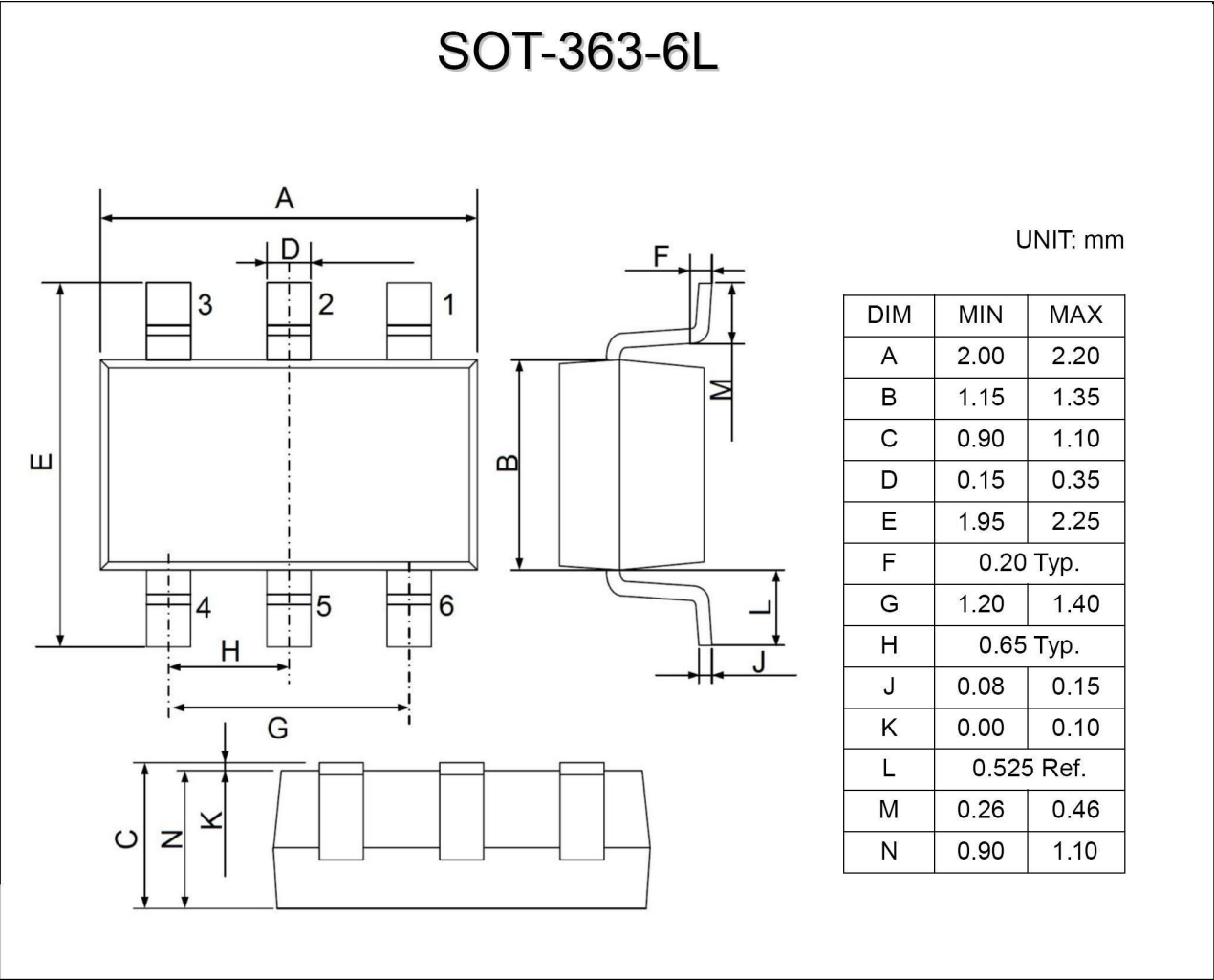
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector-Base Breakdown Voltage	V _{CBO}	I _C = 10μA I _E = 0	80			V
Collector-Emitter Breakdown Voltage	V _{CEO}	I _C = 10mA I _B = 0	65			V
Emitter-Base Breakdown Voltage	V _{EBO}	I _E = 10μA I _C = 0	6.0			V
Collector Cut-Off Current	I _{CBO}	V _{CB} = 30V I _E = 0			15	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} = 5V I _C = 0			500	nA
DC Current Gain	h _{FE}	V _{CE} = 5.0V I _C = 2.0mA	200		450	
Collector to Emitter Saturation Voltage	V _{CE(sat)(1)}	I _C = 10mA I _B = 0.5mA			0.1	V
	V _{CE(sat)(2)}	I _C = 100mA I _B = 5.0mA			0.3	V
Base to Emitter Saturation Voltage	V _{BE(sat)}	I _C = 10mA I _B = 0.5mA		0.77		V
Transition Frequency	f _T	V _{CB} = 5.0V f = 100MHz I _E = 10mA	100			MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V f = 1.0MHz I _E = 0			1.5	pF

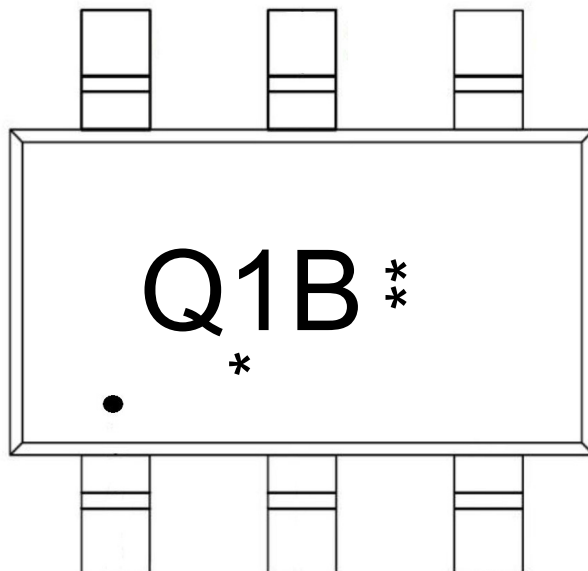
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions



印章说明 / Marking Instructions



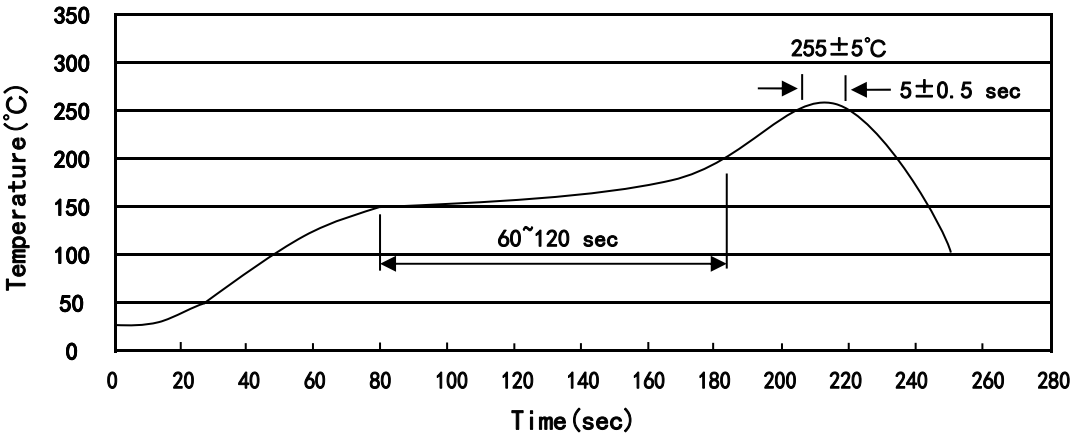
说明：

- ：为“1”脚
Q：为汽车无卤产品标识
1B：为型号代码
***：为生产批号代码，随生产批号变化

Note:

- ：“1” Pin
Q: Automobile halogen-free product Code
1B: Product Type Code
***: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



- 说明：

 - 1、预热温度 150 ~ 200℃，时间 60 ~ 120sec;
 - 2、峰值温度 255±5℃，时间持续为 5±0.5sec;
 - 3、焊接制程冷却速度为 2 ~ 10℃/sec.
- Note:

 - 1.Preheating:150~200℃, Time:60~120sec.
 - 2.Peak Temp.:255±5℃, Duration:5±0.5sec.
 3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃ 时间：10±1 sec. Temp.:260±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-363	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices